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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 20	0.017 at $V_{GS} = -4.5 \text{ V}$	- 12		
	0.020 at V _{GS} = - 2.5 V	- 11		
	0.024 at V _{GS} = - 1.8 V	- 10.1		

PowerPAK SO-8 6.15 mm 5.15 mm 2 3 4 Bottom View

Ordering Information: Si7983DP-T1-E3 (Lead (Pb)-free)

Si7983DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

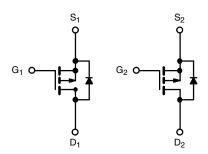
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile



COMPLIANT
HALOGEN
FREE

APPLICATIONS

· Load Switch



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unles	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I _D	- 12	- 7.7	А
Continuous Diain Current (1) = 150 C)	T _A = 70 °C		- 9.6	- 6.2	
Pulsed Drain Current		I _{DM}	- 30		^
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.9 - 1.2		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.5	1.4	W
Maximum Power Dissipation	T _A = 70 °C		2.2	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)b, c			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	26	35	
Maximum Junction-to-Ambient	Steady State		60	85	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	2.2	2.7	

Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Vishay Siliconix



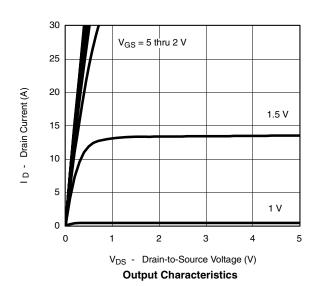
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -600 \mu A$	- 0.40		- 1	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V	-1				
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 5	- μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 30			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 12 A		0.014	0.017	Ω	
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 11 A		0.016	0.020		
		V _{GS} = - 1.8 V, I _D = - 4.1 A		0.020	0.024		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 12 A		41		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 2.9 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			49	74		
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -12 \text{ A}$		7.2		nC	
Gate-Drain Charge	Q_{gd}			12.1			
Gate Resistance	R_g	f = 1 MHz		8		Ω	
Turn-On Delay Time	t _{d(on)}			35	55		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		60	90	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		390	585		
Fall Time	t _f			190	285		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.9 A, dI/dt = 100 A/μs		106	160		

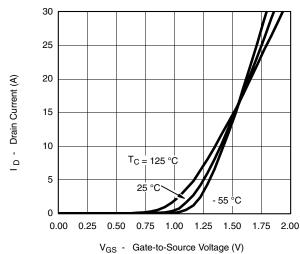
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





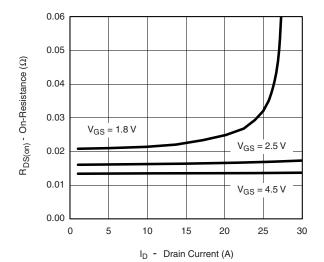
Transfer Characteristics



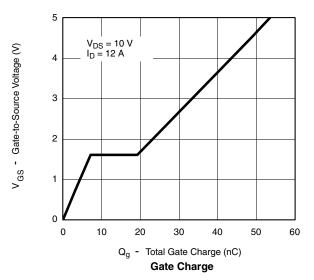


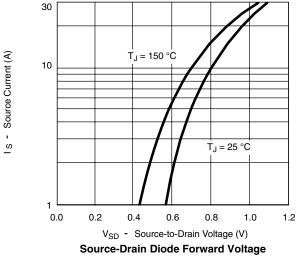


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



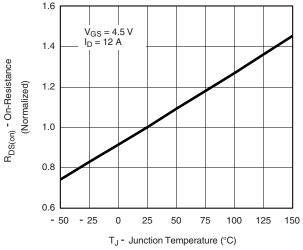


6000 5000 $\mathsf{C}_{\mathsf{iss}}$ C - Capacitance (pF) 4000 3000 2000 Coss 1000 C_{rss} 0 8 20 0 12 16

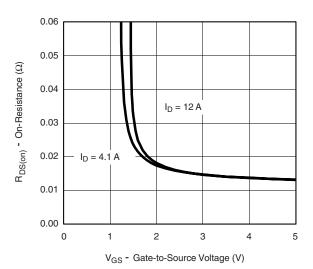
V_{DS} - Drain-to-Source Voltage (V)

Capacitance





On-Resistance vs. Junction Temperature

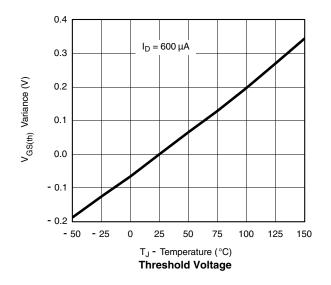


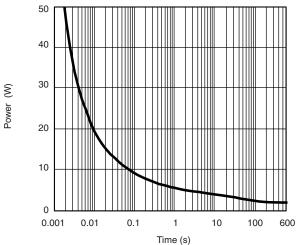
On-Resistance vs. Gate-to-Source Voltage

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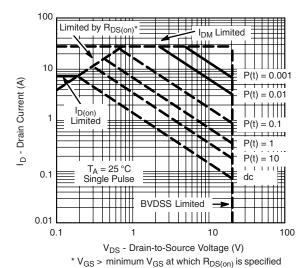
VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

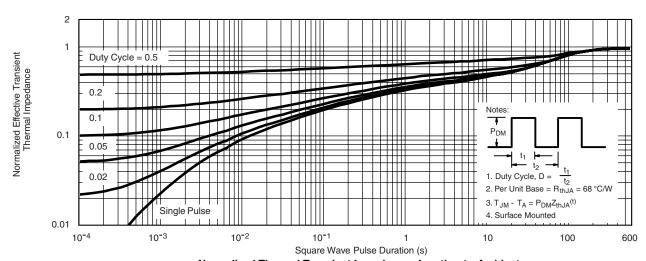




Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

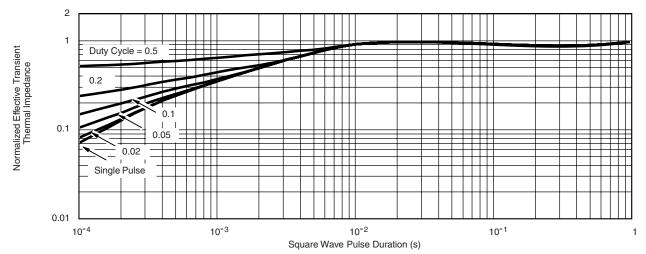


Normalized Thermal Transient Impedance, Junction-to-Ambient





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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